

Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. <b>16459-006001</b>	Application No. <b>10/723,987</b>
	Applicant <b>Alexei A. Erchak et al.</b>		
	Filing Date <b>November 26, 2003</b>	Group Art Unit	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
MC	AA	5,359,345	10/25/94	Hunter et al.			
	AB	5,631,190	05/20/97	Negley et al.			
	AC	5,724,062	03/03/98	Hunter et al.			
	AD	5,799,924	07/14/98	Krames et al.			
	AE	5,955,749	09/21/99	Joannopoulos et al.			
	AF	6,071,795	06/06/00	Cheung et al.			
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	AH	6,559,075	05/06/03	Kelly et al.			
	AI	6,410,942	06/25/02	Thibeault et al.			
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Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AP	WO 98/14986	04/09/98	PCT				

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
MC	AQ	W.S. Wong et al. "Damage-free separation of GaN thin films from sapphire substrates", Appl. Phys. Lett. 72 (5), February 2, 1998, pages 599-601
MC	AR	M.K. Kelly et al. "Optical process for liftoff of Group III-nitride films", Physica Status Solidi; Rapid Research Note, November 28, 1996, 2 pages.
MC	AS	A. A. Erchak et al. "Enhanced coupling to vertical radiation using a two-dimensional photonic crystal in a semiconductor light-emitting diode", Appl. Phys. Lett. (78 (5), January 29, 2001, pages 563-565

Examiner Signature 	Date Considered <b>12/20/04</b>
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 16459-006001	Application No. 10/723,987
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Alexei A. Erchak et al.	
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Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
ML	AT	P.L. Gourley et al. "Optical properties of two-dimensional photonic lattices fabricated as honeycomb nanostructures in compound semiconductors", Appl. Phys. Lett. 64(6), February 7, 1994, pages 687-689
ML	AU	P.L. Gourley et al. "Optical Bloch waves in a semiconductor photonic lattice", Appl. Phys. Lett. 60 (22), June 1, 1992, pages 2714-2716
ML	AV	J.R. Wendt et al. "Nanofabrication of photonic lattice structures in GaAs/AlGaAs", J. Vac. Sci. Technol. B 11(6), November/December 1993, pages 2637-2640
ML	AW	M. Krames et al "Introduction to the Issue on High-Efficiency Light-Emitting Diodes", IEEE Journal on selected topic in quantum electronics, Vol. 8, No. 2 March/April 2002, pages 185-188
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ML	ABB	M. Zelsmann et al. "Seventy-fold enhancement of light extraction from a defectless photonic crystal made on silicon-on-insulator", Appl. Phys. Lett. 83 (13), September 29, 2003, pages 2542-2544
ML	ACC	M. Rattier et al. "Omnidirectional and compact guided light extraction from Archimedean photonic lattices", Appl. Phys. Lett. 83 (7), August 18, 2003, pages 1283-1285
ML	ADD	Y.-J. Lee et al. "A high-extraction-efficiency nanopatterned organic light-emitting diode", Appl. Phys. Lett. 82(21), May 26, 2003, pages 3779-3781
ML	AEE	I. Schnitzer et al. "30% external quantum efficiency from surface textured, thin-film light-emitting diodes", Appl. Phys. Lett. 63 (18), October 18, 1993, pages 2174-2176
ML	AFF	M. Boroditsky et al. "Light extraction from optically pumped light-emitting diode by thin-slab photonic crystals", Appl. Phys. Lett. 75 (8), August 23, 1999, pages 1036-1038
ML	AGG	L. Chen et al. "Fabrication of 50-100 nm Patterned InGaN Blue Light Emitting Heterostructures", Phys. Stat. Sol. (a), 188 (1), 2001, pages 135-138.
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ML	AJJ	M.K. Kelly et al. "Optical patterning of GaN films", Appl. Phys. Lett 68 (12), September 16, 1996, pages 1749-1751

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